

10/540303  
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FORM PTO-1449	SERIAL NO. <del>Not Yet Assigned</del> 10/540,303	CASE NO. 9905/30 (BIF023241/US)
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE Herewith	GROUP ART UNIT <del>Not Yet Assigned</del> 2823
APPLICANTS: FOURNEL et al.		

REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER Number-Kind Code (if known)	DATE	NAME	CLASS/ SUBCLASS	FILING DATE
<i>Le</i>	A1	US 2001/0007367 A1	07/12/2001	Ohkubo		
	A2	6,096,433	08/01/2000	Kikuchi et al.		
	A3	6,013,954	01/11/2000	Hamajima		
	A4	5,661,316	08/26/1997	Kish, Jr. et al.		
	A5	5,138,422	08/11/1992	Fujii et al.		
<i>Le</i>	A6	4,920,396	04/24/1990	Shinohara et al.		

FOREIGN PATENT DOCUMENT

EXAMINER INITIAL		DOCUMENT NUMBER Number-Kind Code (if known)	DATE	COUNTRY	CLASS/ SUBCLASS	TRANSLATION YES OR NO
<i>Le</i>	A7	FR 2 819 099 A1	12/28/2000	France		no
	A8	EP 0 889 509 A2	01/07/1999	EPO		

EXAMINER INITIAL	OTHER ART - NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)					
<i>Le</i>	A9	K.Y. Ahn et al., "Growth, Shrinkage, And Stability Of Interfacial Oxide Layers Between Directly Bonded Silicon Wafers," published In Applied Physics A, 50, 1990, pp. 85-94).				
	A10	D.M. Garnier et al., "The Fabrication Of A Partial Soi Substrate," Proceedings Of The 9th International Symposium On Silicon On Isolator Technology And Devices, 1999, Vol. 99, Ch. 54, pp. 73-78.				
	A11	A. Laporte et al., "Charged Defects At The Interface Between Directly Bonded Silicon Wafers."				
	A12	T.Y. Tan et al., "On Oxygen Precipitation Retardation/Recovery Phenomena, Nucleation Incubation Phenomena, And The Exigent-Accommodation-Volume Factor Of Precipitation," Proceedings Of The Fifth International Symposium On Silicon Materials Science And Technology; Semiconductor Silicon 198 Electrochem, Soc, Pennington, NJ, USA; 1986, pp. 864-73).				
	A13	K. Terada et al., "A New Dram Cell With A Transistor On A Lateral Epitaxial Silicon Layer (Tole Cell)," published In IEEE Transactions On Electron Device, Vol. 37, N° 9, Sept. 1990, pp. 2052-7.				
<i>Le</i>	A14	H. Yamaguchi et al, "Intelligent Power IC With Partial Soi Structure," published In Jpn, J. Appl. Phys. Vol. 34 (1995), pp. 864-868.				

EXAMINER <i>Le</i>	DATE CONSIDERED 12/10/07
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.